

## NJ903L Process

### Silicon Junction Field-Effect Transistor

- Low-Current
- Low Gate Leakage Current
- High Input Impedance

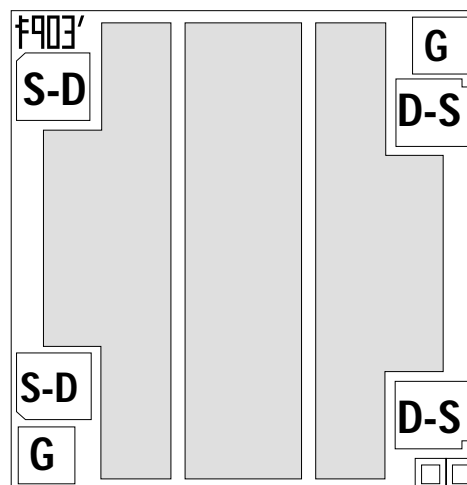
#### Absolute maximum ratings at 25 °C free-air temperature.

Gate Current, $I_g$	10 mA
Operating Junction Temperature, $T_j$	+150°C
Storage Temperature, $T_s$	- 65°C to +175°C

Device in this Databook based on the NJ903L Process.

#### Datasheet

IF9030



Die Size = 0.040" X 0.040"  
 All Bond Pads = 0.004" Sq.  
 Substrate is also Gate.

At 25°C free air temperature:

#### Static Electrical Characteristics

		NJ903L Process						
		Min	Typ	Max	Unit	Test Conditions		
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	- 20	- 25		V	$I_G = - 1 \mu A, V_{DS} = 0V$		
Reverse Gate Leakage Current	$I_{GSS}$		- 5	- 500	pA	$V_{GS} = - 15V, V_{DS} = 0V$		
Drain Saturation Current (Pulsed)	$I_{DSS}$	5		500	mA	$V_{DS} = 10V, V_{GS} = 0V$		
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	- 0.1		- 3	V	$V_{DS} = 10V, I_D = 1 nA$		

#### Dynamic Electrical Characteristics

Input Capacitance	$C_{iss}$		50		pF	$V_{DS} = 0V, V_{GS} = - 10V$	$f = 1 MHz$
Feedback Capacitance	$C_{rss}$		18		pF	$V_{DS} = 0V, V_{GS} = - 10V$	$f = 1 MHz$
Equivalent Noise Voltage	$\hat{e}_N$		0.5		nV/ $\sqrt{HZ}$	$V_{DG} = 4V, I_D = 5 mA$	$f = 1 kHz$



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